

# BCV65

# NPN/PNP general-purpose transistor Rev. 4 — 27 July 2010

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

NPN/PNP general-purpose transistor in a small SOT143B Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pair
- AEC-Q101 qualified
- Small SMD plastic package

## 1.3 Applications

General-purpose switching and amplification

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor; for the PNP transisto	r with negative polarity				
$V_{CEO}$	collector-emitter voltage	open base	-	-	30	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	75	-	800	

#### **Pinning information** 2.

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1, 3	collector		
2	common base	4 3	1
4	common emitter	1 2	2 4 3 006aab228



## NPN/PNP general-purpose transistor

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BCV65	-	plastic surface-mounted package; 4 leads	SOT143B

## 4. Marking

Table 4. Marking codes

Type number	Marking code[1]
BCV65	97*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor; for the PNP transistor with	h negative polarity			
$V_{CBO}$	collector-base voltage	open emitter	-	30	V
$V_{CEO}$	collector-emitter voltage	open base	-	30	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current		-	200	mA
$I_{BM}$	peak base current		-	200	mA
Per devic	е				
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$	-	250	mW
Tj	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-65	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

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## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB).

## 7. Characteristics

Table 7. Characteristics

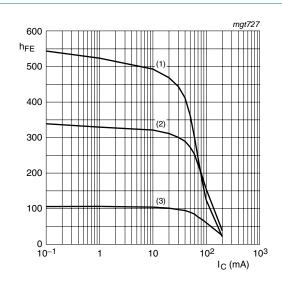
 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	Per transistor; for the PNP transistor with negative polarity					
I <sub>CBO</sub> collector-base cur current	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$	-	-	15	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	5	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	75	-	800	
OLSat	collector-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	-	90	300	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	-	250	650	mV
DESat	base-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	[1] -	700	-	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	<u>[1]</u> -	900	-	mV
V <sub>BE</sub>	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	[2] 580	650	750	mV
		I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V	[2] -	-	820	mV

<sup>[1]</sup>  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.

<sup>[2]</sup>  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

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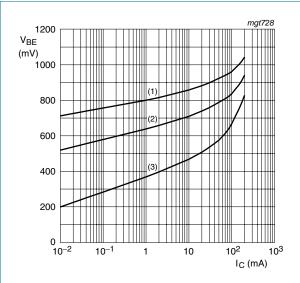
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



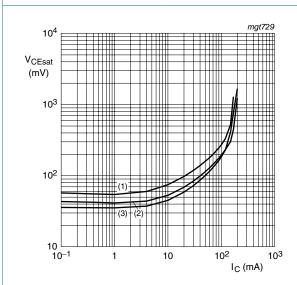
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 2. TR1 (NPN): Base-emitter voltage as a function of collector current; typical values

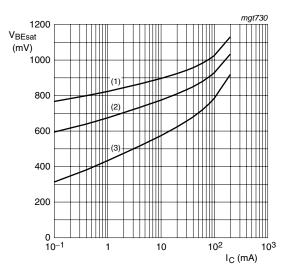


$$I_{\rm C}/I_{\rm B}=20$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

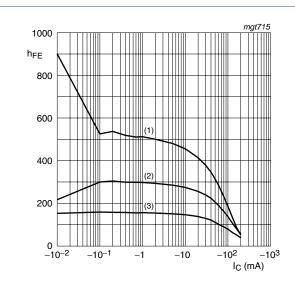
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. TR1 (NPN): Base-emitter saturation voltage as a function of collector current; typical values

#### NPN/PNP general-purpose transistor



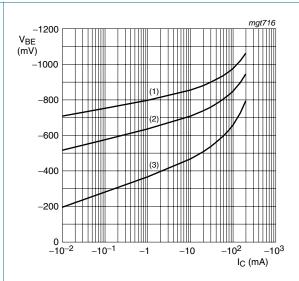
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. TR2 (PNP): DC current gain as a function of collector current; typical values



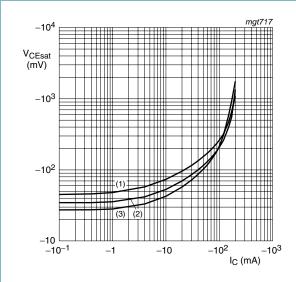
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 6. TR2 (PNP): Base-emitter voltage as a function of collector current; typical values



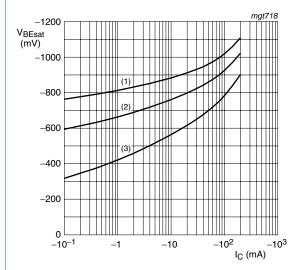
$$I_{\rm C}/I_{\rm B}=20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 8. TR2 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

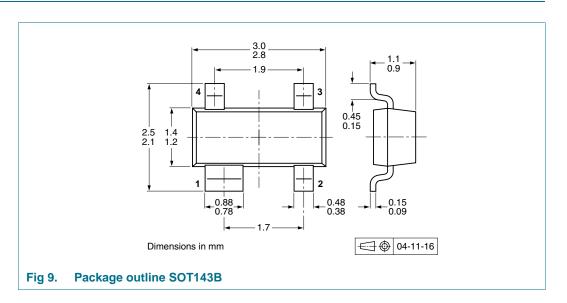
#### NPN/PNP general-purpose transistor

## 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



# 10. Packing information

Table 8. Packing methods

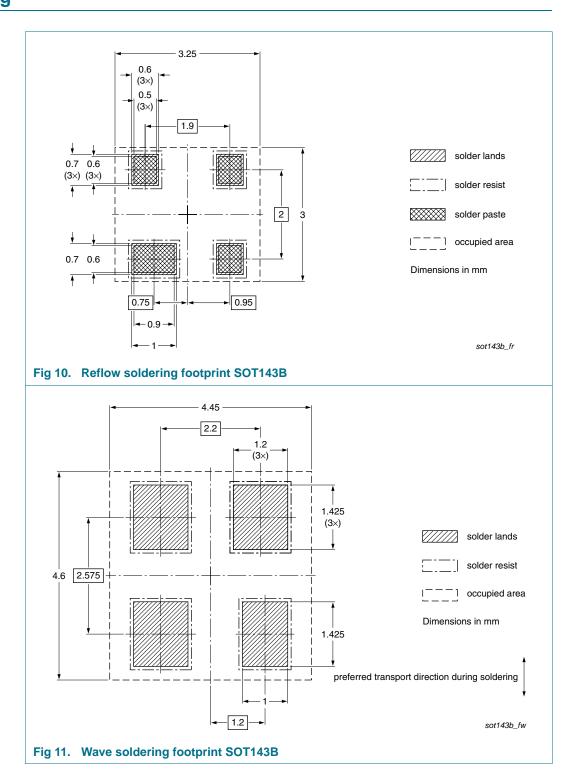
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BCV65	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section 14}}$ .

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# 11. Soldering



## NPN/PNP general-purpose transistor

# 12. Revision history

Table 9. Revision history

Release date	Data sheet status	Change notice	Supersedes		
20100727	Product data sheet	-	BCV65_3		
		redesigned to comply v	vith the new identity		
<ul> <li>Legal texts</li> </ul>	have been adapted to the n	ew company name whe	ere appropriate.		
<ul> <li>Section 1 "F</li> </ul>	Product profile": amended				
<ul> <li>Section 3 "C</li> </ul>	Ordering information": added	t			
Section 4 "Marking": updated					
• <u>Figure 1, 2, 3, 4, 5, 6, 7</u> and <u>8</u> : added					
<ul> <li>Figure 9: superseded by minimized package outline drawing</li> </ul>					
<ul> <li>Section 8 "Test information": added</li> </ul>					
<ul> <li>Section 10 "Packing information": added</li> </ul>					
Section 11 "Soldering": added					
Section 13	"Legal information": updated	d .			
19990422	Product specification	-	BCV65_CNV_2		
19970422	Product specification	-	-		
	20100727  The format guidelines of Legal texts Section 1 "F Section 3 "C Section 4 "N Figure 1, 2, Figure 9: su Section 10 " Section 11 " Section 13 " 19990422	<ul> <li>Product data sheet</li> <li>The format of this data sheet has been guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the none section 1 "Product profile": amended</li> <li>Section 3 "Ordering information": added</li> <li>Section 4 "Marking": updated</li> <li>Figure 1, 2, 3, 4, 5, 6, 7 and 8: added</li> <li>Figure 9: superseded by minimized pactions and section 10 "Packing information": added</li> <li>Section 10 "Packing information": added</li> <li>Section 11 "Soldering": added</li> <li>Section 13 "Legal information": updated</li> <li>Product specification</li> </ul>	<ul> <li>Product data sheet -</li> <li>The format of this data sheet has been redesigned to comply viguidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name who section 1 "Product profile": amended</li> <li>Section 3 "Ordering information": added</li> <li>Section 4 "Marking": updated</li> <li>Figure 1, 2, 3, 4, 5, 6, 7 and 8: added</li> <li>Figure 9: superseded by minimized package outline drawing</li> <li>Section 8 "Test information": added</li> <li>Section 10 "Packing information": added</li> <li>Section 11 "Soldering": added</li> <li>Section 13 "Legal information": updated</li> <li>19990422 Product specification -</li> </ul>		

#### NPN/PNP general-purpose transistor

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#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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#### NPN/PNP general-purpose transistor

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